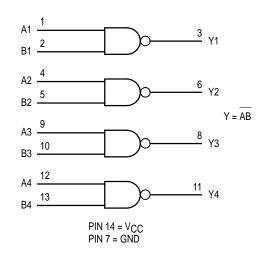
Quad 2-Input NAND GateHigh-Performance Silicon-Gate CMOS

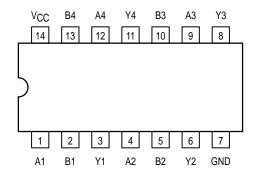
The MC54/74HC00A is identical in pinout to the LS00. The device inputs are compatible with Standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

- Output Drive Capability: 10 LSTTL Loads
- · Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 32 FETs or 8 Equivalent Gates

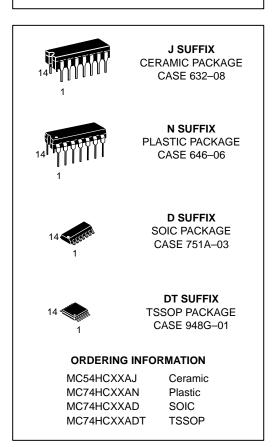
LOGIC DIAGRAM



Pinout: 14-Lead Packages (Top View)



MC54/74HC00A



FUNCTION TABLE

Inputs		Output
Α	В	Y
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

10/95

REV 7

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
Vcc	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package Ceramic DIP	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or VCC).

Unused outputs must be left open.

Ceramic DIP: - 10 mW/°C from 100° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
VCC	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GNI	0)	Vcc	V
TA	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time	V 0	1000 500 400	ns

^{*} Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

DC CHARACTERISTICS (Voltages Referenced to GND)

			v _{CC}	Guara	nteed Lim	nit	
Symbol	Parameter	Condition	V	–55 to 25°C	≤85°C	≤125°C	Unit
VIH	Minimum High-Level Input Voltage	$V_{out} = 0.1V$ or $V_{CC} -0.1V$ $ I_{out} \le 20\mu A$	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	>
VIL	Maximum Low-Level Input Voltage	$V_{out} = 0.1V$ or $V_{CC} - 0.1V$ $ I_{out} \le 20\mu A$	2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	>
VOH	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{aligned} V_{\text{in}} = & V_{\text{IH}} \text{ or } V_{\text{IL}} & I_{\text{out}} \leq 2.4 \text{mA} \\ & I_{\text{out}} \leq 4.0 \text{mA} \\ & I_{\text{out}} \leq 5.2 \text{mA} \end{aligned} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
VOL	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu A$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	٧
		$\begin{aligned} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & & I_{\text{out}} \leq 2.4 \text{mA} \\ & I_{\text{out}} \leq 4.0 \text{mA} \\ & I_{\text{out}} \leq 5.2 \text{mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	±0.1	±1.0	±1.0	μΑ
ICC	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\mu A$	6.0	1.0	10	40	μА

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

		vcc	Guaranteed Limit			
Symbol	Parameter	v	–55 to 25°C	≤85°C	≤125°C	Unit
^t PLH [,] ^t PHL	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns
tTLH, tTHL	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 27 15 13	95 32 19 16	110 36 22 19	ns
C _{in}	Maximum Input Capacitance		10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, $V_{CC} = 5.0 \text{ V}$, $V_{EE} = 0 \text{ V}$	
C_{PD}	Power Dissipation Capacitance (Per Buffer)*	22	pF

^{*} Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

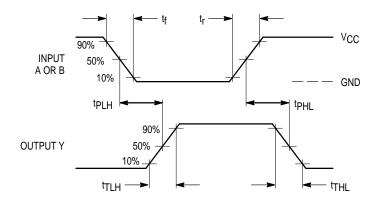
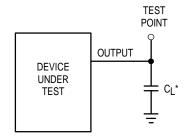


Figure 1. Switching Waveforms



*Includes all probe and jig capacitance

Figure 2. Test Circuit

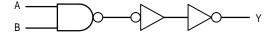
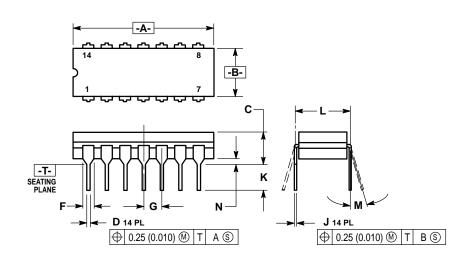


Figure 3. Expanded Logic Diagram (1/4 of the Device)

OUTLINE DIMENSIONS

J SUFFIX

CERAMIC DIP PACKAGE CASE 632-08 ISSUE Y

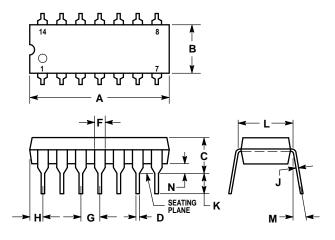


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
 4. DIMESNION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC RODY.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.750	0.785	19.05	19.94	
В	0.245	0.280	6.23	7.11	
С	0.155	0.200	3.94	5.08	
D	0.015	0.020	0.39	0.50	
F	0.055	0.065	1.40	1.65	
G	0.100 BSC		2.54	BSC	
J	0.008	0.015	0.21	0.38	
K	0.125	0.170	3.18	4.31	
L	0.300	BSC	7.62 BSC		
М	0°	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

N SUFFIX

PLASTIC DIP PACKAGE CASE 646-06 ISSUE L



NOTES:

- NOTES:

 1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.

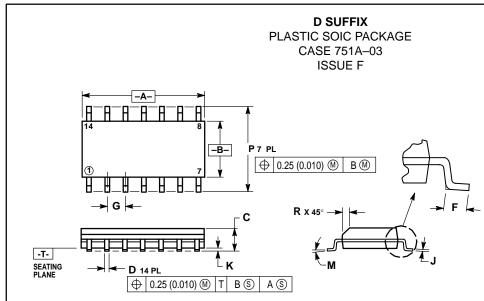
 2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.

 3. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

 4. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54 BSC	
Н	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300	0.300 BSC		BSC
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01

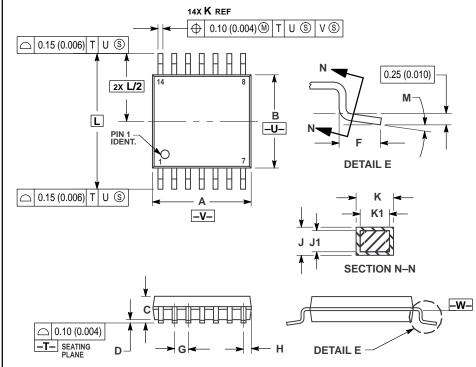
OUTLINE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

DT SUFFIX PLASTIC TSSOP PACKAGE CASE 948G-01 **ISSUE O**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15
- (0.006) PER SIDE.
 DIMENSION B DOES NOT INCLUDE INTERLEAD
 FLASH OR PROTRUSION. INTERLEAD FLASH OR
 PROTRUSION SHALL NOT EXCEED
- 0.25 (0.010) PER SIDE.
 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN
 EXCESS OF THE K DIMENSION AT MAXIMUM
 MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65 BSC		0.026 BSC		
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
M	0°	8°	0°	8°	

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MC54/74HC00A/D

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